## IN THE SPECIFICATION:

1. (withdrawn) A method of forming electrical connection members on an electrical structure comprising the steps of:

providing an electrical structure with a set of contacts;

forming at least one interface layer adhering to said set of contacts;

patterning said interface layer to form a set of pads disposed over said set of contacts;

depositing and lithographically patterning a layer of photoresist with a set of apertures over

said set of pads;

forming a set of conductive pins adhering directly to said pad;

forming a barrier layer adhering to all exposed surfaces of said set of pins;

forming a layer of solder surrounding the barrier layer; and

reflowing the layer of solder.

- 2. (withdrawn) A method according to claim 1, in which the material of the barrier layer blocks passage of material from the pins, thereby preventing the material from the pins from reacting with a constituent of the solder.
- 3. (withdrawn) A method according to claim 1, in which the interface layer comprises a layer of adhesion material and a seed layer.

- 4. (withdrawn) A method according to claim 2, in which the interface layer comprises a layer of adhesion material and a seed layer.
- 5. (withdrawn) A method according to claim 1, in which the interface layer includes material selected from the group comprising TiW, Ti, Ta, Cr and TaN.
- 6. (withdrawn) A method according to claim 2, in which the interface layer includes material selected from the group comprising TiW, Ti, Ta, Cr and TaN.
- 7. (withdrawn) A method according to claim 3, in which the interface layer includes material selected from the group comprising TiW, Ti, Ta, Cr and TaN.
- 8. (withdrawn) A method according to claim 4, in which the interface layer includes material selected from the group comprising TiW, Ti, Ta, Cr and TaN.
- 9. (withdrawn) A method according to claim 1, in which the pins are formed by electroplating material into the apertures in the photoresist.
- 10. (withdrawn) A method according to claim 1, in which the pins are plated with a wetting layer before the step of forming a layer of solder.

- 11. (withdrawn) A method according to claim 10, in which the material of the barrier layer blocks passage of material from the pins, thereby preventing the material from the pins from reacting with a constituent of the solder.
- 12. (withdrawn) A method according to claim 10, in which the interface layer comprises a layer of adhesion material and a seed layer.
- 13. (withdrawn) A method according to claim 11, in which the interface layer comprises a layer of adhesion material and a seed layer.
- 14. (original) An electrical structure containing electrical connection members adapted for connecting to another electrical structure comprising:
- a first set of contacts in an electrical structure;
- at least one interface layer adhering to said set of contacts;
- a set of pads disposed over said set of contacts and including said interface layer;
- a set of conductive pins adhering directly to said pads;
- a barrier layer adhering to all exposed surfaces of said set of pins; and
- a layer of solder surrounding the barrier layer.

- 15. (original) A structure according to claim 14, in which the material of the barrier layer blocks passage of material from the pins, thereby preventing the material from the pins from reacting with a constituent of the solder.
- 16. (original) A structure according to claim 14, in which the interface layer comprises a layer of adhesion material and a seed layer.
- 17. (original) A method according to claim 15, in which the interface layer comprises a layer of adhesion material and a seed layer.
- 18. (original) A method according to claim 14, in which the interface layer includes material selected from the group comprising TiW, Ti, Ta, Cr and TaN.
- 19. (original) A method according to claim 15, in which the interface layer includes material selected from the group comprising TiW, Ti, Ta, Cr and TaN.
- 20 (original) A method according to claim 14, in which a wetting layer selected from the group comprising Cu and Au is formed on the barrier layer.